



Is Now Part of



To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor



74VCX163245

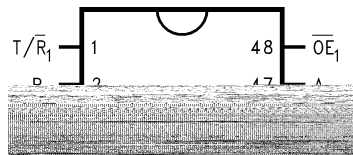
Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

Features

74VCX163245 Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

Connection Diagram

Pin Assignment for TSSOP



Pin Assignment for FBGA

(Top Thru View)

FBGA Pin Assignments

	1	2	3	4	5	6
A	B_0	NC	T/\bar{R}_1	$\bar{O}E_1$	NC	A_0
B	B_2	B_1	NC	NC	A_1	A_2
C	B_4	B_3	V_{CCB}	V_{CCA}	A	

Pin Descriptions

Logic Diagram

Truth Tables

Inputs		Outputs
\overline{OE}_1	T/\overline{R}_1	
L	L	Bus B ₀ –B ₇ Data to Bus A ₀ –A ₇
L	H	Bus gU7 9 rn70.4944 0 TD 0.2164 Tw (must bta to (2us Tf 10 0)Tj 0 0 0 1 8l1 538 rntar944 0 TD 0.2164 Tw (must

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial (HIGH or LOW, inputs may not float)

Z = High Impedance

VCX163245 Translator Power Up Sequence Recommendations

To guard against power up problems, some simple guidelines need to be adhered to. The VCX163245 is designed so that the control pins (T/\overline{R}_n , \overline{OE}_n) are supplied by V_{CCB} . Therefore the first recommendation is to begin by powering up the control side of the device, V_{CCB} . The \overline{OE}_n control pins should be ramped with or ahead of V_{CCB} , this will guard against bus contentions and oscillations as all A Port and B Port outputs will be disabled. To ensure the high impedance state during power up or power down, \overline{OE}_n should be tied to V_{CCB} through a pull up resistor. The minimum value of the resistor is determined by the current sourcing capability of the driver. Second, the T/\overline{R}_n control pins should be

placed at logic LOW (0V) level, this will ensure that the B-side bus pins are configured as inputs to help guard against bus contention and oscillations. B-side Data Inputs should be driven to a valid logic level (0V or V_{CCB}), this will prevent excessive current draw and oscillations. V_{CCA} can then be powered up after V_{CCB} , however V_{CCA} must be greater than or equal to V_{CCB} to ensure proper device operation. Upon completion of these steps the device can then be configured for the users desired operation. Following these steps will help to prevent possible damage to the translator device as well as other system components.

Logic Diagrams

Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

74VCX163245 Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

DC Electrical Characteristics ($1.65V < V_{CCB} \leq 1.95V$, $2.3V < V_{CCA} \leq 2.7V$)

Symbol	Parameter	V_{CCB} (V)	V_{CCA} (V)	Conditions	Min.	Max.	Units
V_{IHA}	HIGH Level Input Voltage	A_n	1.65–1.95	2.3–2.7		1.6	V
V_{IHB}		$B_n, \overline{T/R}, \overline{OE}$	1.65–1.95	2.3–2.7		$0.65 \times V_{CCB}$	V
V_{ILA}	LOW Level Input Voltage	A_n	1.65–1.95	2.3–2.7		0.7	V
V_{ILB}		$B_n, \overline{T/R}, \overline{OE}$	1.65–1.95	2.3–2.7		$0.35 \times V_{CCB}$	V
V_{OHA}	HIGH Level Output Voltage		1.65–1.95	2.3–2.7	$I_{OH} = -100\mu A$	$V_{CCA} - 0.2$	V
			1.65	2.3–2.7	$I_{OH} = -18mA$	1.7	
V_{OHB}	HIGH Level Output Voltage		1.65–1.95	2.3–2.7	$I_{OH} = -100\mu A$	$V_{CCB} - 0.2$	V
			1.65–1.95	2.3	$I_{OH} = -6mA$	1.25	
V_{OLA}	Low Level Output Voltage		1.65–1.95	2.3–2.7	$I_{OL} = 100\mu A$	0.2	V
			1.65	2.3–2.7	$I_{OL} = 18mA$	0.6	
V_{OLB}	Low Level Output Voltage		1.65–1.95	2.3–2.7	$I_{OL} = 100\mu A$	0.2	V
			1.65–1.95	2.3	$I_{OL} = 6mA$	0.3	
I_I	Input Leakage Current @ \overline{OE} , $\overline{T/R}$		1.65–1.95	2.3–2.7	$0V \leq V_I \leq 3.6V$	± 5.0	μA
I_{OZ}	3-STATE Output Leakage		1.65–1.95	2.3–2.7	$0V \leq V_O \leq 3.6V$, $\overline{OE} = V_{CCB}$, $V_I = V_{IH}$ or V_{IL}	± 10	μA
I_{OFF}	Power Off Leakage Current		0	0	$0 \leq (V_I, V_O) \leq 3.6V$	10	μA
I_{CCA}/I_{CCB}	Quiescent Supply Current, per supply, V_{CCA} / V_{CCB}		1.65–1.95	2.3–2.7	$A_n = V_{CCA}$ or GND, B_n, \overline{OE} , & $\overline{T/R} = V_{CCB}$ or GND	20	μA
			1.65–1.95	2.3–2.7	$V_{CCA} \leq A_n \leq 3.6V$, $V_{CCB} \leq B_n, \overline{OE}$, $\overline{T/R} \leq 3.6V$	± 20	μA
ΔI_{CC}	Increase in I_{CC} per Input, $B_n, \overline{T/R}, \overline{OE}$ Increase in I_{CC} per Input, A_n		1.65–1.95	2.3–2.7	$V_I = V_{CCB} - 0.6V$	750	μA

DC Electrical Characteristics ($1.65V < V_{CCB} \leq 1.95V$, $3.0V < V_{CCA} \leq 3.6V$)

Symbol	Parameter	V_{CCB} (V)	V_{CCA} (V)	Conditions	Min.	Max.	Units
V_{IHA}	HIGH Level Input Voltage	A_n	1.65–1.95	3.0–3.6		2.0	V
V_{IHB}		$B_n, \overline{T/R}, \overline{OE}$	1.65–1.95	3.0–3.6		$0.65 \times V_{CCB}$	V
V_{ILA}	LOW Level Input Voltage	A_n	1.65–1.95	3.0–3.6		0.8	V
V_{ILB}		$B_n, \overline{T/R}, \overline{OE}$	1.65–1.95	3.0–3.6		$0.35 \times V_{CCB}$	V
V_{OHA}	HIGH Level Output Voltage		1.65–1.95	3.0–3.6	$I_{OH} = -100\mu A$	$V_{CCA} - 0.2$	V
			1.65	3.0–3.6	$I_{OH} = -24mA$	2.2	
V_{OHB}	HIGH Level Output Voltage		1.65–1.95	3.0–3.6	$I_{OH} = -100\mu A$	$V_{CCA} - 0.2$	V
			1.65–1.95	3.0	$I_{OH} = -6mA$	1.25	
V_{OLA}	LOW Level Output Voltage		1.65–1.95	3.0–3.6	$I_{OL} = 100\mu A$	0.2	V
			1.65	3.0–3.6	$I_{OL} = 24mA$	0.55	
V_{OLB}	LOW Level Output Voltage		1.65–1.95	3.0–3.6	$I_{OL} = 100\mu A$	0.2	V
			1.65–1.95	3.0	$I_{OL} = 6mA$	0.3	
I_I	Input Leakage Current @ \overline{OE} , $\overline{T/R}$	1.65–1.95	3.0–3.6	$0V \leq V_I \leq 3.6V$		± 5.0	μA
I_{OZ}	3-STATE Output Leakage	1.65–1.95	3.0–3.6	$0V \leq V_O \leq 3.6V$, $\overline{OE} = V_{CCB}$, $V_I = V_{IH}$ or V_{IL}		± 10	μA
I_{OFF}	Power OFF Leakage Current	0	0	$0 \leq (V_I, V_O) \leq 3.6V$		10	μA
I_{CCA}/I_{CCB}	Quiescent Supply Current, per supply, V_{CCA}/V_{CCB}		1.65–1.95	3.0–3.6	$A_n = V_{CCA}$ or GND, B_n, \overline{OE} , & $\overline{T/R} = V_{CCB}$ or GND	20	μA
			1.65–1.95	3.0–3.6	$V_{CCA} \leq A_n \leq 3.6V$, $V_{CCB} \leq B_n, \overline{OE}$, $\overline{T/R} \leq 3.6V$	± 20	
ΔI_{CC}	Increase in I_{CC} per Input, $B_n, \overline{T/R}, \overline{OE}$,	1.65–1.95	3.0–3.6	$V_I = V_{CCB} - 0.6V$		750	μA
	Increase in I_{CC} per Input, A_n	1.65–1.95	3.0–3.6	$V_I = V_{CCA} - 0.6V$		750	

DC Electrical Characteristics ($2.3V < V_{CCB} \leq 2.7V$, $3.0V \leq V_{CCA} \leq 3.6V$)

Symbol	Parameter	V_{CCB} (V)	V_{CCA} (V)	Conditions	Min.	Max.	Units
V_{IHA}	HIGH Level Input Voltage	A_n	2.3–2.7	3.0–3.6		2.0	V
V_{IHB}			$B_n, \overline{T/R}, \overline{OE}$	2.3–2.7	3.0–3.6	1.6	V
V_{ILA}	LOW Level Input Voltage	A_n	2.3–2.7	3.0–3.6		0.8	V
V_{ILB}			$B_n, \overline{T/R}, \overline{OE}$	2.3–2.7	3.0–3.6	0.7	V
V_{OHA}	HIGH Level Output Voltage		2.3–2.7	3.0–3.6	$I_{OH} = -100\mu A$	$V_{CCA} - 0.2$	V
			2.3	3.0–3.6	$I_{OH} = -24mA$	2.2	V
V_{OHB}	HIGH Level Output Voltage		2.3–2.7	3.0–3.6	$I_{OH} = -100\mu A$	$V_{CCB} - 0.2$	V
			2.3–2.7	3.0	$I_{OH} = -18mA$	1.7	V
V_{OLA}	LOW Level Output Voltage		2.3–2.7	3.0–3.6	$I_{OL} = 100\mu A$	0.2	V
			2.3	3.0–3.6	$I_{OL} = 24mA$	0.55	V
V_{OLB}	LOW Level Output Voltage		2.3–2.7	3.0–3.6	$I_{OL} = 100\mu A$	0.2	V
			2.3–2.7	3.0	$I_{OL} = 18mA$	0.6	V
I_I	Input Leakage Current @ \overline{OE} , $\overline{T/R}$	2.3–2.7	3.0–3.6	$0V \leq V_I \leq 3.6V$		± 5.0	μA
I_{OZ}	3-STATE Output Leakage @ A_n	2.3–2.7	3.0–3.6	$0V \leq V_O \leq 3.6V$, $\overline{OE} = V_{CCA}$, $V_I = V_{IH}$ or V_{IL}		± 10	μA
I_{OFF}	Power OFF Leakage Current	0	0	$0 \leq (V_I, V_O) \leq 3.6V$		10	μA
I_{CCA}/I_{CCB}	Quiescent Supply Current, per supply, V_{CCA}/V_{CCB}		2.3–2.7	3.0–3.6	$A_n = V_{CCA}$ or GND, B_n, \overline{OE} , & $\overline{T/R} = V_{CCB}$ or GND	20	μA
			2.3–2.7	3.0–3.6	$V_{CCA} \leq A_n \leq 3.6V$, $V_{CCB} \leq B_n, \overline{OE}$, $\overline{T/R} \leq 3.6V$	± 20	μA
ΔI_{CC}	Increase in I_{CC} per Input, $B_n, \overline{T/R}, \overline{OE}$		2.3–2.7	3.0–3.6	$V_I = V_{CCB} - 0.6V$	750	μA
			2.3–2.7	3.0–3.6	$V_I = V_{CCA} - 0.6V$	750	μA

AC Electrical Characteristics

$T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $C_L =$

Symbol	Parameter
--------	-----------

Note:

7. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{osHL}) or LOW-to-HIGH (t_{osLH}).

Dynamic Switching Characteristics

Capacitance

Symbol	Parameter	Conditions	T _A = +25°C	Units
C _{IN}	Input Capacitance	V _{CCB} = 2.5V, V _{CCA} = 3.3V, V _I = 0V or V _{CCA/B}	5	pF
C _{I/O}	Input/Output Capacitance	V _{CCB} = 2.5V, V _{CCA} = 3.3V, V _I = 0V or V _{CCA/B}	6	pF
C _{PD}	Power Dissipation Capacitance	V _{CCB} = 2.5V, V _{CCA} = 3.3V, V _I = 0V or V _{CCA/B} , f = 10MHz	20	pF

AC Loading and Waveforms

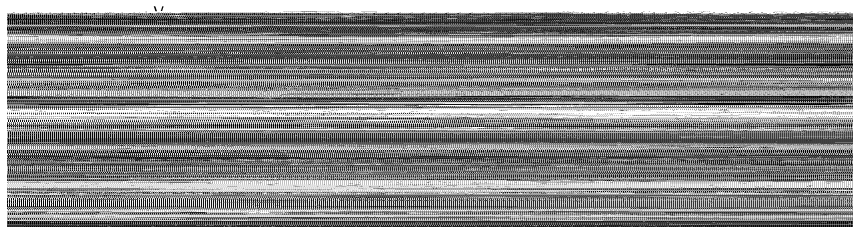


Figure 1. AC Test Circuit

Test	Switch
t _{PLH} , t _{PHL}	OPEN
t _{PZL} , t _{PLZ}	6V at V _{CC} = 3.3 ± 0.3V; V _{CC} × 2 at V _{CC} = 2.5 ± 0.2V; 1.8V ± 0.15V
t _{PZH} , t _{PHZ}	GND

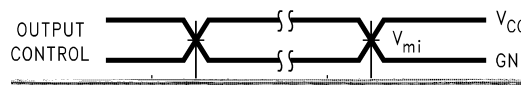


Figure 4. 3-STATE Output Low Enable and Disable Times for Low Voltage Logic
t_R = t_F ≤ 2.0 ns, 10% to 90%



Figure 2. Waveform for Inverting and Non-inverting Functions
t_R = t_F ≤ 2.0 ns, 10% to 90%



Figure 3. 3-STATE Output High Enable and Disable Times for Low Voltage Logic
t_R = t_F ≤ 2.0 ns, 10% to 90%

Symbol	V _{CC}		
	3.3V ± 0.3V	2.5V ± 0.2V	1.8V ± 0.15V
V _{mi}	1.5V	V _{CC} / 2	V _{CC} / 2
V _{mo}	1.5V	V _{CC} / 2	V _{CC} / 2
V _X	V _{OL} + 0.3V	V _{OL} + 0.15V	V _{OL} + 0.15V
V _Y	V _{OH} - 0.3V	V _{OH} - 0.15V	V _{OH} - 0.15V

Physical Dimensions

Dimensions are in millimeters unless otherwise noted.

Physical Dimensions (Continued)

Dimensions are in millimeters unless otherwise noted.




Figure 6. 48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide Package Number MTD48



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx [®]	<i>i-Lo</i> [™]	Power-SPM [™]	TinyBoost [™]
Across the board. Around the world. [™]	ImpliedDisconnect [™]	PowerTrench [®]	TinyBuck [™]
ActiveArray [™]	IntelliMAX [™]	Programmable Active Droop [™]	TinyLogic [®]
Bottomless [™]	ISOPLANAR [™]	QFET [®]	TINYOPTO [™]
Build it Now [™]	MICROCOUPLER [™]	QS [™]	TinyPower [™]
CoolFET [™]	MicroPak [™]	QT Optoelectronics [™]	TinyWire [™]
CROSSVOLT [™]	MICROWIRE [™]	Quiet Series [™]	TruTranslation [™]
CTL [™]	Motion-SPM [™]	RapidConfigure [™]	μSerDes [™]
Current Transfer Logic [™]	MSX [™]	RapidConnect [™]	UHC [®]
DOME [™]	MSXPro [™]	ScalarPump [™]	UniFET [™]
E ² CMOS [™]	OCX [™]	SMART START [™]	VCX [™]
EcoSPARK [®]	OCXPro [™]	SPM [®]	Wire [™]
EnSigna [™]	OPTOLOGIC [®]	STEALTH [™]	
FACT Quiet Series [™]	OPTOPLANAR [®]	SuperFET [™]	
FACT [®]	PACMAN [™]	SuperSOT [™] 3	
FAST [®]	PDP-SPM [™]	SuperSOT [™] 6	
FASTr [™]	POP [™]	SuperSOT [™] 8	
FPST [™]	Power220 [®]	SyncFET [™]	
FRFET [®]	Power247 [®]	TCM [™]	
GlobalOptoisolator [™]	PowerEdge [™]	The Power Franchise [®]	
GTO [™]	PowerSaver [™]		
HiSeC [™]			

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor. The datasheet is printed for reference information only.

Rev. I26

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf